PCI	N Numb	er:	20230426	5001.	2		PCI	N Da	te:	April 28, 2023	
TAL		Qualifica	tion of new	/ Fab	Fab sites (MIHO8 & AIZU) using qualified Process Technology,						
Title	e:	-			I Malaysia as additio		•			<b>- - - -</b>	
Cus	tomer	Contact:	-	<b>PCN</b>	Manager		Dep	ot:		Quality Services	
Pro	posed 1	1 <sup>st</sup> Ship D	ate:	Oct	28, 2023	Sample accepte	-		;	May 28, 2023*	
*Sa	mple real	quests rec	eived after	r May 28, 2023 will not be supported							
Cha	nge Ty	pe:									
$\boxtimes$	Assem	bly Site		$\boxtimes$	Assembly Process			$\boxtimes$	Assembly Materials		
	Design	1		Electrical Specification					Mecha	anical Specification	
$\boxtimes$	Test S	ite		Packing/Shipping/Labeling				Test F		Process	
	Wafer	Bump Site	u		Wafer Bump Material				Wafer	Bump Process	
$\boxtimes$	Wafer	Fab Site			Wafer Fab Materials				Wafer	· Fab Process	
					Part number chang	e					

#### **PCN Details**

#### **Description of Change:**

Texas Instruments is pleased to announce the qualification of a new fab site (MH8 & Aizu) and TI Malaysia as additional Assembly and Test Site for selected devices as listed below in the product affected section. Additionally, LBC8LVISO has been qualified as an additional process technology.

C	urrent Fab Site	9	Additional Fab Site					
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter			
DMOS5	HPA07	200 mm	Aizu	HPA07	200 mm			
DMOS5	HPA07ISOS	200mm	MH8	LBC8LVISO	200mm			

#### Construction Differences are noted below:

	TAI	MLA
Wire type	Au, 0.96 mil	1mil Cu (Die to LF) 0.96mil Au (Die to Die)

#### **Marking Differences:**

	Current Device Symbolization	New Device Symbolization
**ECAT	Include Value	Remove
TI Bug	Include	Replace with "TI" text
Example	130101 2023754 AHS7	XÌĴODBQL TI LCK CEK4

\*\* - Not all devices necessarily have ECAT information included in the symbolization, but for the ones that do, this information will be removed.

Test coverage, insertions, conditions will remain consistent with current testing and verified with test  $\ensuremath{\mathsf{MQ}}$ 



AMC1301-Q1 SBAS792B – APRIL 2017 – REVISED APRIL 2023

# Changes from March 13, 2023 to April 24, 2023 (from Revision A (April 2017) to Revision B (April 2023))

(F	April 2023))	age
•	Changed document title	
•	Changed Features section: Changed, deleted, and reorganized bullets	1
•	Added Functional-Safety-Capable bullet to Features section	1
•	Changed isolation standard from DIN VDE V 0884-11 (VDE V 0884-10) to DIN EN IEC 60747-17 (VDE	
	0884-17) and updated the Insulation Specifications and Safety-Related Certifications tables accordingly	1
•	Changed the Description section to include common-mode decoupling capacitors as a known best practic	
•	Changed pin names VINP to INP, VINN to INN, VOUTP to OUTP, and VOUTN to OUTN throughout	
	document	4
•	Changed Description column and added footnotes to Pin Functions table	4
•	Changed PD from 81.4 mW to 99 mW	6
•	Changed PD1 (VDD1 = 3.3 V) from 24.85 mW to 31 mW	6
•	Changed PD1 (VDD1 = 5.5 V) from 45.65 mW to 54 mW	
•	Changed PD2 (VDD2 = 3.3 V) from 20.16 mW to 26 mW	
•	Changed PD2 (VDD2 = 5.5 V) from 35.75 mW to 45 mW	6
•	Changed DTI from ≥0.027 mm to ≥0.021 mm in Insulation Specifications table	7
•	Changed I <sub>IB</sub> parameter specification and conditions	9
•	Changed IDD1 (3.0 V ≤ VDD1 ≤ 3.6 V) from 5.0 mA (typ) / 6.9 mA (max) to 6.3 mA (typ) / 8.5 mA (max)	9
•	Changed IDD1 (4.5 V ≤ VDD1 ≤ 5.5 V) from 5.9 mA (typ) / 8.3 mA (max) to 7.2 mA (typ) / 9.8 mA (max)	9
•	Changed IDD2 (3.0 V ≤ VDD2 ≤ 3.6 V) from 4.4 mA (typ) / 5.6 mA (max) to 5.3 mA (typ) / 7.2 mA (max)	9
•	Changed IDD2 (4.5 V ≤ VDD2 ≤ 5.5 V) from 4.8 mA (typ) / 6.5 mA (max) to 5.9 mA (typ) / 8.1 mA (max)	
•	Changed Timing Diagram section	10
•	Changed Input Bias Current vs Common-Mode Input Voltage figure to align with new test condition	12
•	Changed Input Bias Current vs High-Side Supply Voltage figure to align with new test condition	12
•	Changed Input Bias Current vs Temperature figure to align with new test condition	
•	Changed legend of Output Voltage vs Input Voltage figure, VOUTP is now red and VOUTN is now black	12
•	Changed Overview section	
•	Changed Functional Block Diagram image	19
•	Changed the Analog Input section	19
•	Added the Isolation Channel Signal Transmission section	20
•	Added Analog Output section, deleted Fail-Safe Output section	21
•	Changed Device Functional Modes section	21
•	Changed Application Information section	
•	Changed Typical Application section	
•	Changed Best Design Practices section	
•	Changed Power Supply Recommendations section	
•	Changed the Recommended Layout of the AMC1301-Q1 figure	
•	Added a link to the Isolated Voltage-Measurement Circuit in the Related Documentation section	27

#### The datasheet number will be changing.

Device Family	Change From:	Change To:	URL
AMC1301-Q1	SBAS792A	SBAS792B	http://www.ti.com/product/ AMC1301-Q1

# Reason for Change:

Continuity of supply.

- 1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
- 2) Maximize flexibility within our Assembly/Test production sites.
- 3) Cu is easier to obtain and stock

# Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None

#### Impact on Environmental Ratings

D

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings. RoHS REACH **Green Status IEC 62474** No Change No Change No Change No Change Changes to product identification resulting from this PCN: **Fab Site Information:** Chip Site Origin Chip Site Country Chip Site City Chip Site Code (20L) Code (21L) DMOS5 DM5 USA Dallas MH8 JPN Ibaraki MIHO8 AIZU CU<sub>2</sub> **JPN** Aizuwa kamatsu-shi Assembly Site Information: Assembly Site Origin Assembly Country Code Assembly Site Assembly City (22L) (23L) TAI TAI TWN Chung Ho, New Taipei City **MLA MLA** MYS **Kuala Lumpur** Sample product shipping label (not actual product label) TEXAS INSTRUMENTS (Pb (1P) SN74LS07NSR MADE IN: Malaysia 2DC: 20: (a) 2000 (D) 0336 31T)LOT: 3959047MLA MSL 2 /260C/1 YEAR SEAL DT 4W) TKY(1T) 7523483SI2 MSL 1 /235C/UNLIM 03/29/04 P) OPT: ITEM: 2P) REV: 0033317 (V) (21L) 11.000 5A (L)T0:1750 (201 LBL: 22L) ASO: MLA (23L) ACO: MYS Group 1 Product Affected: (Fab site, Data Sheet & MLA A/T) AMC1301QDWVRQ1 Group 2 Product Affected: (Fab site, Data Sheet) AMC1301QDW VQ1

# Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 06-April-2023

#### **Product Attributes**

Attributes	Qual Device:	Qual Device:	QBS Process Reference:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:	QBS Product Reference:	QBS Product Reference:	QBS Product Reference:
Autorita	AMC1301QDWVRQ1 (TAI)	AMC1301QDWVRQ1 (MLA)	INA215AQDCKRQ1	AMC1305M25QDWRQ1	AMC1336DWV	AMC1300BQDWVRQ1	AMC1300BQDWVRQ1	AMC1300BQDWVRQ1	AMC1311CQDWVRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Signal Chain	Signal Chain
Wafer Fab Supplier	AIZU, AIZU, MH8, MH8	AIZU, AIZU, MH8, MH8	AIZU	AIZU, MH8, MH8	AIZU, AIZU, MH8, MH8	DP1DM5, DP1DM5, AIZU	MH8, MH8, AIZU, AIZU	MH8, MH8, AIZU, AIZU	MH8, MH8, AIZU, AIZU
Assembly Site	TAI	MLA	TFME	TAI	TAI	TAI	TAI	MLA	MLA
Package Group	SOIC	SOIC	SOT	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DWV	DWV	DCK	DWV	DWV	DW	DWV	DWV	DWV
Pin Count	8	8	6	8	8	16	8	8	8

QBS: Qual By Similarity

Qual Device AMC1301QDWVRQ1 is qualified at MSL3 260C

Qual Device AMC1301QDWVRQ1 is qualified at MSL3 260C

### Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

					Duiu D	iopia, o	u uo.			ai campio	3120 / 1010	i ianoa		
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: AMC1301QDWVRQ1 <u>(TAI)</u>	Qual Device: AMC1301QDWVRQ1 (MLA)	QBS Process Reference: INA215AQDCKRQ1	QBS Process Reference: <u>AMC1305M25QDWRQ1</u>	QBS Package Reference: <u>AMC1336DWV</u>	QBS Product Reference: <u>AMC1300BQDWVRQ1</u>	QBS Product Reference: AMC1300BQDWVRC
Test Group	A - Acce	lerated Environ	Iment St	tress Tes	sts		·			•	•			
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL3 260C	1 Step	-	-	-	-	3/0/0	1/0/0	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours		-	-		3/231/0	1/77/0	-
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	-	-	3/231/0	1/77/0	-
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	-	-	-	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	-	3/231/0	1/77/0	-
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	-	-	-	1/5/0	1/5/0	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	-	1/45/0	1/45/0	-
Test Group B	B - Acce	lerated Lifetime	e Simula	tion Tes	ts									
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	140C	480 Hours	-	-	-	-	-	1/77/0	
HTOL	В1	JEDEC JESD22- A108	1	77	Life Test	150C	408 Hours	-	-	-	-	-	-	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-	-	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	150C	24 Hours	-	-	-	3/2400/0	-	-	-
Test Group (	C - Pack	age Assembly	Integrity	Tests										
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	-	-	3/90/0	1/30/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	-	-	3/90/0	1/30/0	1/30/0
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	-	1/15/0 (1)	-	-
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	1/15/0 (1)	-	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-		-	3/10/0 (2)	-	-
Test Group [	D - Die F	abrication Relia	ability Te	sts										
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

Туре	#	Test Spec	Min Lot	SS /	Test Name	Condition	Duration	Qual Device:	Qual Device:	QBS Process Reference:	QBS Process Reference:	QBS Package Reference:	QBS Product Reference:	QBS Product Reference:
			Qty	Lot				AMC1301QDWVRQ1 (TAJ)	AMC1301QDWVRQ1 (MLA)	INA215AQDCKRQ1	AMC1305M25QDWRQ1	AMC1336DWV	AMC1300BQDWVRQ1	AMC1300BQDWV
IDDB	D2	JESD35		-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
СІ	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
IBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
м	D5		-	-	Stress Migration	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technolog Requirements
est Group	E - Elect	trical Verificatio	n Tests											
SD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	-	-	-	-	-	-	1/3/0
SD	E2	AEC Q100- 002	1	3	ESD HBM	-	4000 Volts	-	-	-	-	-	1/3/0	-
SD	E3	AEC Q100- 011	1	3	ESD CDM	-	1500 Volts	-	-	-	-	-	1/3/0	-
SD	E3	AEC Q100- 011	1	3	ESD CDM	-	750 Volts	-	-	-	-	-	-	1/3/0
U	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	-	-	-	-	-	1/6/0	1/6/0
D	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold		-	-		-	-	3/90/0	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles **Ambient Operating Temperature by Automotive Grade Level:** 

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Note (1): Pb & Pb-Free Solderability data from MSPREL.12.UCD8220.04001

Note (2): Physical Dimensions data from QID 20171030-123810

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

# Automotive New Product Qualification Summary

(As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

Approve Date 06-Apr-2023

		Data	a Disi	blaye	d as: Number	of lots / I otal s	sample s	ize / I otal failed	
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>AMC1301QDWVRQ1</u> ( <u>MLA)</u>	QBS Reference: AMC1311CQDWVRQ1
Test G	roup A - A	Accelerated Environme	ent Stres	s Tests					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	1 Step	-	3/0/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	-	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	-	3/66/0
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	3/3/0
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	3/9/0
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-	3/9/0

### **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Texas Instruments Incorporated

TI Information – Selective Disclosure

PCN#20230426001.2

HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires		3/9/0
HAST	A2.2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	192 Hours	-	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed		3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed		3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	-	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	-	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires		3/9/0
тс	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	3/66/0
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	3/3/0
тс	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	3/9/0
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-	3/9/0
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-	3/9/0
тс	A4.2	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	-	3/210/0
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	3/66/0
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	3/3/0
тс	A4.2.3		3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	-	3/9/0
тс	A4.2.4		3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	-	3/9/0
тс	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	-	3/9/0
HTSL	A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	3/3/0
HTSL	A6.2	JEDEC JESD22- A103	3	45	High Temperature Storage Life	175C	1000 Hours	-	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	3/3/0
Test Gr	oup B - A	Accelerated Lifetime Si	mulation	Tests					
Test Gr	oup C - F	ackage Assembly Inte	egrity Tes	sts					
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	3/30/0
Test Gr	oup D - D	ie Fabrication Reliabili	ity Tests						
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

QBS: Qual By Similarity

Qual Device AMC1301QDWVRQ1 is qualified at MSL3 260C

Qual Device AMC1301QDWVRQ1 is qualified at MSL3 260C

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150 C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles **Ambient Operating Temperature by Automotive Grade Level:** 

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C Grade 3 (or I) : -40C to +85C

E1 (TEST): Électrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

ZVEI ID reference: SEM-PA-18, SEM-PA-08, SEM-PA-13, SEM-TF-01, SEM-PW-13, SEM-DS-01

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	PCN ww admin team@list.ti.com

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